Evidence of two-dimensional macroscopic quantum tunneling of a current-biased DC-SQUID

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The escape probability out of the superconducting state of a hysteretic DC - SQUD has been m easured at di erent values of the applied magnetic ux. At low tem perature, the escape current and the width of the probability distribution are tem perature independent but they depend on ux. Experimental results do not t the usual one-dimensional (1D) Macroscopic Quantum Tunneling (MQT) law but are perfectly accounted for by the two-dimensional (2D) MQT behaviour as we propose here. Near zero ux, our data con rm s the recent MQT observation in a DC-SQUD [14].

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Quantum dynamics of a current-biased Josephson junction (JJ) have been extensively studied during the past two decades [1]. The phase di erence across the JJ obeys the same dynamics as the position of a ctitious particle moving in a one dimensional tilted washboard potential, whose average slope is proportional to the current bias. For bias below the critical current, the particle is trapped in a local m in im um . It can escape out by Thermal Activation (TA) or by Macroscopic Quantum Tunneling (MQT). Many experiments have dem onstrated these two escape regimes. Quantized energy levels and resonant activation have been observed by applying m icrow aves [1, 4]. Very recently R abi oscillations and coherent temporal oscillations were observed in a current biased JJ [2, 3] or in a Cooperpair transistor coupled to a biased JJ [5]. Experiments on RF-SQUID have also clearly dem onstrated quantum dynamics in form of MQT [1], resonant tunneling or quantum superposition of states [6].

By contrast and surprisingly, very few studies have been performed in a current biased DC-SOUD in the quantum regime. The dynamics of a DC-SQUID are described by two degrees of freedom and new phenomena can arise. The ctitious particle moves in this case in a two-dimensional (2D) potential. At zero magnetic eld it has been predicted that escape out of a localm in im um can occur via two di erent trajectories [7, 8]. At non zero magnetic eld, MQT was derived only in the limit of sm all inductance of the loop [9], where the SQUD is nearly equivalent to a single junction with a uxdependent critical current. In this case, the dynam ics are one dim ensional. To our know ledge only three previous experiments were reported in the past discussing escape from a current-biased DC-SQUD. In the TA regime good agreem ent with 2D transition state theory [10] has been obtained [11]. Sim ilar results were obtained in an RF-SQUID [12]. In the quantum regime no experimental evidence of two-dimensional behaviour has been demonstrated up to now. Shari et al. [13] claim ed MQT observations but neither the amplitude of quantum uctuations nor the TA regime were understood. Recent

m easurements [14] have clearly observed MQT and TA regimes in a DC-SQUID at zero magnetic eld. 2D behaviour could, however, not be observed because at zero ux the escape rate of their SQUID behaves exactly as that of a single Josephson junction, ie. a 1D system . Understanding the dynamics of a hysteretic DC-SQUID is very important in interpreting some recent quantum experiments [15, 16], or a recently proposed experiment of a one shot quantum measurement in a superconducting charge qubit using a DC-SQUID [17].

In this letter, we report on an escape m easurem ent in a DC-SQUID both in the therm al and in the quantum regime. In contrast to till now reported results on MQT, 1D tunneling escape form ula can not describe our experim ental data. Since no theory has described MQT in a DC-SQUID in the 2D regime at non zero magnetic ux, we propose a method based on the zero magnetic eld result derived in Ref. [7] but taking into account the ux dependence of the 2D potential. O ur experim ental data support quantitatively this approach.

The current-biased DC-SQUID consists of two Josephson junctions in parallel in an inductive superconducting loop. The whole system has two degrees of freedom described by $'_1$ and $'_2$, the phase di erence across the two junctions. A ssum ing identical JJs, each having a critical current equal to I₀ and a capacitance equal to C₀, the dynamics of the system can be treated as that of a ctitious particle moving in a two dimensional potential given by [18]

$$U(x;y) = U_0 \quad sx \quad cosx \, cosy \quad sy + b(y = _0)^2$$
(1)

where $U_0 = {}_0I_0 = is$ the sum of the Josephson energy of the two JJs, $s = I_{D C} = (2I_0)$, $x = ('_1 + '_2)=2$, $y = ('_1 '_2)=2$, $b = {}_0=(2 L I_0)$ and $I_{D C}$ is the bias current. The asymmetry of inductances is parametrized by $= (L_2 L_1)=L$ where L_1 and L_2 are the inductances of the two branches and $L = L_1 + L_2$ is the inductance of the SQUID bop. is the applied ux and ${}_0 = h=2e$ is the ux quantum.

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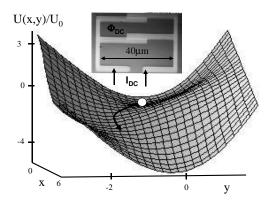


FIG.1: Bidim ensional potential of our SQUID which has parameters s = 0.7, $= _0 = _027$ and $b = _0.6$ and $= _0.26$. The particle and its escape path are drawn as illustration. Inset: photograph of the type of a DC-SQUID used in the experiment.

The potential presents valleys and m ountains with bcalminima separated by saddle points along which the particle can escape. The barrier height between the minim a and the saddle points depends on the bias current and m agnetic ux and vanishes at the critical current I_c . I_c follows the usual ux dependence with $_0$ periodicity. In the following we consider b 1 close to that of our DC-SQUID. In this limit, there exists only one optim al trajectory that passes through the saddle point. Therefore we will not discuss escape out of a localminimum through two di erent trajectories [7, 8]. Yet the 2D signature still exists because the optim al trajectory is not a straight line along the x-direction but follows a path in the landscape with the tilt in the potential.

In the limits . s_c where $s_c = I_c = (2I_0)$ is the normalized e ective critical current of the DC-SQUID, we can expand the potential (Eq. (1)) to the third order. The escape occurs in a current and ux dependent angle with respect to the x-axis. A long this direction, we obtain the potential barrier height, U = $U_0 r s_c \cos^3 = u (1 + \tan)^{3-2}$, and the plasma frequency, $!_{p} = !_{p0} (u \cos = s_{c})^{1-4} (1 + \tan)^{1-4}$ where u is the third derivative of the potential along the escape direction [11]. The quantities $!_{p0} = 2^{1=4}$ ($I_c = {}_0C_0$)¹⁼² (1) $s=s_c)^{1=4}$ and U₀ = $(4^{r} \overline{2}=3) (_0=2) I_c (1 s=s_c)^{3=2}$ are the usual plasm a frequency and potential height, respectively, of a single JJ with an e ective critical current I_c and a capacitance 2C₀. The 2D character of the escape is exhibited in these expressions by the renorm alization of the plasm a frequency and the potential barrier height of a single JJ. Therefore the ratios $!_p = !_{p0}$ and $U = U_0$ show deviations from 1D behavior.

U sing the previous results of the renorm alized plasm a frequency and potential height, the escape rate out of a 2D potential well, in the TA regime, ^{TA}, is predicted to

be [10]

$${}^{TA} = \frac{!_{p}}{2} \frac{!_{w?}}{!_{s?}} \exp - \frac{U}{k_{B}T}$$
 (2)

where $!_{w?}$ and $!_{s?}$ are respectively the transverse frequency modes in the well and at the saddle point [11]. We numerically analyzed the modulation of the escape current as a function of ux in the TA regime taking into account the transverse frequency modes in the escape rate. For our SQUID parameters, the deviation of $!_{w?} = !_{s?}$ from unity has been estimated to be 2% at zero ux and it quickly decreases to zero when increasing $j = _0 j$. Since this small error appears only in the prefactor of Eq. (2), we will assume in the following that $!_{w?} = !_{s?} = 1$.

At low tem perature, the escape is dom insted by quantum tunneling. This regime has been theoretically studied at zero ux in [7, 8] discussing the splitting of the two escape trajectories, or ux dependence in the low inductance limit (b >> 1) [9]. There is so far, to our knowledge, no theoretical treatment of ux dependence of 2D MQT, i.e. in the regime b. 1. Therefore we propose to use the MQT escape rate at zero magnetic ux [7, 14] in the limit b 1. We introduce in this escape rate, MQT, the 2D behaviour by taking the plasm a frequency $!_p$ and the potential barrier height U along the escape direction, analogously to what was done in the TA regime earlier [11]:

$${}^{M \ Q \ T} = f_{2D} \frac{!_{p}}{2} q \frac{1}{864} = \frac{1}{2} \exp(36 \ U = 5^{2} !_{p});$$
(3)

This 2D MQT rate thus depends on the magnetic ux and on the bias-current. In the following, because b 1, two escape trajectories are in possible and f_{2D} ' 1. Note, however, that the 2D behaviour remains through U and ! p. At zero magnetic ux ^{MQT} equals that of a single JJ of critical current $2I_0$ and capacitance $2C_0$.

The escape probability P_{esc} from the zero voltage state during time t is a function of the amplitude of the bias current, the ux and temperature. M easured escape probability using current DC-pulses of duration t = 50 s is plotted in Fig. 3. Each point corresponds to 4000 current pulses. By increasing the bias current, P_{esc} starts from zero far below the critical current where the barrier is high, and it becomes unity at currents close to and above the critical one. In the following the escape current I_{esc} is de ned as the bias current corresponding to $P_{esc} = 0.5$ and the width of the escape probability distribution I as the difference between the currents at $P_{esc} = 0.9$ and $P_{esc} = 0.1$. The measured escape rate is extracted from $(I_{D\,C}) = \ln (1 P_{esc} (I_{D\,C})) = t$ and it ranges from about 10 s 1 to 10^5 s 1 (inset of Fig. 2).

The sample is a DC-SQUID consisting of two A \models A \mid o_x=A ltunnel junctions obtained by e-beam lithography and shadow evaporation (inset of Fig. 1). The area of each JJ is about 11 m². The tunnel resistance

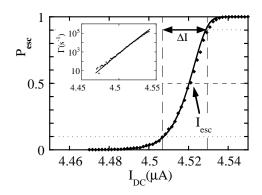


FIG.2: M easured escape probability and escape rate (inset) as functions of the bias current at $=_0 = 0.07$, T = 42 mK and t = 50 s. The dots are experimental data and the lines the MQT prediction of Eq. (3). Values of I_{esc} and I are indicated by dashed lines.

of the SQU \mathbb{D} , R $_{\mathrm{T}}$ ' 80 , and the superconducting gap = 230 eV are deduced from the dissipative branches of the IV characteristic and yield I_0 ' 2:3 A using the Ambeqaokar-Barato relation assuming two identicalJJs. From MQT of a single JJ with the same area, we deduced $C_0 = 0.46 \text{ pF}$, which agrees with the typical specic capacitance of about 50 fF/(m)² for an A $10 \times$ tunnel junction. The rectangular SQUD loop is about 10 m by 40 m giving an estim ated m agnetic inductance of about 70 pH. The kinetic inductance of the SQUID, deduced from the thin lm resistivity, ' 5:3 cm, is coarsely estim ated to be about 120 pH . The total inductance L, the sum of the kinetic and m agnetic inductances, is therefore about 190 pH. An inductance asymmetry exists because the two SQUD branches have di erent lengths. W e estim ate 02 by assuming proportionality between length of a branch and inductance. The im m ediate electrom agnetic environm ent of the DC-SQUID is determined by two 20 nm thin, 1 m wide and 700 m long superconducting alum inium wires term inated by two large pads for wire bonding. The estim ated total inductance of the in-situ wires, $L_e = 4.6$ nH, results again of the sum of 1.2 nH m agnetic inductance of the coplanar strips and of 3.4 nH kinetic inductance of the wires. Although these SQUID parameters have been independently estimated, the accuracy in determining them this way is not su cient. Therefore we extracted the inductance of the DC-SQUID L = 244 pH and its asymmetry = 0.26, the zero-ux, the critical current $I_0 = 2.33$ A and the capacitance $C_0 = 0.46 \, \text{pF}$ from the ux m odulation characteristics of the escape current in the low tem perature regime (see Fig. 3). These param eters are in very good agreem ent with the rough estim ates given above. Ourb = 0.6 is much smaller than b 3 of the earlier works [13, 14] on MQT in a DC-SQUD, indicating that the ctitious particle is much more a ected by the two-dimentionality of the potential.

The sample is enclosed in a cavity with resonances above 15 GHz, and it is anchored to the mixing chamber

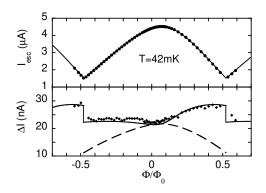


FIG.3: M easured escape current and the width of the probability distribution against external applied ux at low tem – perature (dots). 1D MQT and 2D MQT prediction (Eq. 3) are shown respectively by dashed and solid lines.

of the dilution refrigerator. This cavity is enclosed in a low temperature lter [20] consisting of therm ocoax microw ave lters [19] and - lters. The attenuation of the DC-lines is estim ated to be at least 200 dB above 1 G H z at the mixing cham ber temperature. Therm ocoax lters were also introduced from 1.5 K to the low temperature lter, and low pass LC lters were used at room temperature. Current bias and voltage probe lines of the sam ple are separated from the computer using di erential am pliers. A superconducting shield was inserted inside the vacuum jacket of the cryostat and -m etal surrounds the dewar to protect the DC-SQ U ID from external ux noise. U sing this measurement set-up, we separately measured a width of I = 11 nA on a 1 A Josephson junction in its MQT regime.

Figure 2 shows escape probability and escape rate at $=_0 = 0.07$ and T = 42 mK. At this particular ux value, the escape current ism axim um (see Fig. 3) and the ratios !_p=!_{p0} and U=U₀ are equal to unity. Therefore the SQUID behaves as a single JJ. We can perfectly t our data using 1D MQT predictions (continuous line in Fig. 2) without free param eters which dem onstrates that 1D MQT theory describes the behaviour of a DC -SQUID at the maxim um escape current. This rst result conmon sthe recent MQT observation at zero ux performed by Li et al: [14]. It does not, how ever, dem onstrate 2D escape behaviour.

The escape current and the width versus applied external ux are directly extracted from the measured switching current distribution and they are plotted in Fig. 3 in the MQT regime at T = 42m K. The width is periodic in ux with periodicity $_0$. It is minimum near $= _0 = 0.07$ and increases to reach maximum at $= _0 = 0.5$. There is asymmetry between negative and positive ux values and discountinuities at $= _0 = 0.5$. The usual 1D tunneling model cannot account for the main feature of our results. Namely the 1D model predicts a decrease of the width, I $(2I_0 s_c)^{3=5}$ in the MQT regime (dashed line in Fig. 3) which is contrary to our observation. Our proposed 2D form ula in the MQT

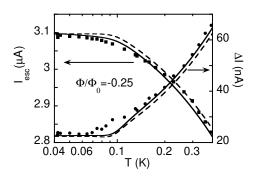


FIG. 4: Measured escape current and width of escape probability distribution I vs. temperature (symbols) at $=_0 = 0.25$ together with predictions when including (continuous line) or excluding (dashed line) the in uence of the environm ent. We assume that the total escape rate is the sum of MQT and TA.

regin e suggests increase of the width and it agrees with our data perfectly also quantitatively. It has no free param eters since all of them were already xed by the escape current characteristics. We claim that these results are the rst experim ental observation of 2D escape from the zero voltage state of a D C -SQ U ID in its M Q T regim e.

The escape current and width against tem perature are shown in Fig. 4 for $= _0 = 0.25$. The escape current increases as tem perature drops and saturates at low tem – perature. The width decreases with tem perature and saturates at low tem perature. These features are perfectly accounted for by Eq. (3) in the MQT regime and by Eq. (2) in the TA regime (dashed lines). Yet the model seem s to underestim ate the measured width in the therm al regime by about 10 %, indicating that in uence of the environment must be taken into account to better t with the data. Finally, the observed cross-over tem pera-

ture (' 80 m K) between M Q T and TA is consistent with that predicted by the well-known formula ~!_p=(2 k_B) [1].

In order to estim ate the e ect of the environm ent on the escape process, we take into account the quadratic current uctuationsh I²i. Since the SQUID is connected to the external circuit through inductive wires on the chip, we assume the electrical environment to be the inductance L_e in series with an external resistor R_{ext} . For tem peratures $k_B T > -R_{ext} = L_e$, the current uctuations are given by h $I^2 i = k_B T = L_e$. For $k_B T < ~!_p$ therm al uctuations are slow as compared to the SQU $\mathbb D$ dynamics, and escape rate can be corrected by $\frac{TA}{env}$ = ^{TA} exp(($0 U = 0 I_{DC}$) h $I^2 i = 2 (k_B T)^2$) in the TA regime and $M_{env}^{M_QT} = M_{QT}^{M_QT} \exp((0 (U = !_p) = 0 I_{DC}) h I^2 i = 2)$ in the MQT regime following the idea in [21]. Using the estim ated wires inductance, our data perfectly are tted both in the quantum and in the TA regime by the uctuation corrected expressions above (continuous line in Fig. 4). W e notice that like in the recent work in [14] the measured I crosses over from MQT to TA much more gradually than what we predict.

In sum mary, we have shown for the rst time evidence of two dimensionalm acroscopic quantum escape of a hysteretic DC-SQUID from its zero voltage state. Moreover, we have proposed a way to theoretically analyze the ux dependence of escape in the MQT regime, and we show that our data perfectly t this model, also in the TA regime with the same values of the circuit parameters.

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